

### **IN THE TITLE**

Please delete the title in its entirety and insert --METHOD FOR TUNING A  
WORK FUNCTION FOR MOSFET GATE ELECTRODES.--

### **IN THE SPECIFICATION**

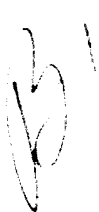
Please delete the abstract in its entirety and insert:

--A method for creating insulated gate field effect transistors having gate electrodes with at least two layers of materials to provide gate electrode work function values that are similar to those of doped polysilicon, to eliminate the poly depletion effect, and to substantially prevent impurity diffusion into the gate dielectric. Depositing bi-layer stacks of relatively thick Al and thin TiN for n-channel FETs and bi-layer stacks of relatively thick Pd and thin TiN, or relatively thick Pd and thin TaN for p-channel FETs is disclosed. Varying the thickness of the thin TiN or TaN layers between a first and second critical thickness may be used to modulate the work function of the gate electrode and thereby obtain the desired trade-off between channel doping and drive currents in FETs--

### **IN THE CLAIMS**

Cancel claims 5 and 14-17 without prejudice.

Please amend the following claims:

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1. (Currently amended) A method of forming a gate electrode, comprising:  
forming a first layer of a first material having a first work function on a  
substrate;